

thermal conductivity, transistors and many other topics are each treated in no more than a page or two of text, while the section on crystal chemistry (less than 50 pages) is almost exclusively descriptive. The work is, indeed, a 'compendium', but it is doubtful whether the student would be able to follow much of the material without the assistance of many supplementary works. Fortunately, references to such works are numerous.

The German translation is better printed and better bound than the Dutch original, but not so much better as to justify a price nearly two and a half times as great. In fact, the price is outrageous, and at 29s. per 100 pages compares very unfavourably with other well known crystallographic works such as Nye's *Physical Properties of Crystals* (16s.), Megaw's *Ferroelectricity in Crystals* (13s.), Born & Huang's *Dynamical Theory of Crystal Lattices* (12s.), and (biggest bargain of all) Wells's *Structural Inorganic Chemistry* (7s.). In any case, however, this translation is likely to be of very limited interest outside of German-speaking countries in view of the fact that an English version is understood to be in an advanced stage of production.

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Growth and Perfection of Crystals: Proceedings of an International Conference on Crystal Growth, Cooperstown, New York, Aug. 1958. Edited by R. H. DOREMUS, B. W. ROBERTS and D. TURNBULL. Pp. 609. London: Chapman and Hall; New York: Wiley. 1958. Price £5-0-0, \$12-50.

To this formidable report 51 authors have contributed and it is only possible to indicate but briefly the content. The report is richly illustrated. The growth of crystal whiskers occupies a relatively large section, for no less than 275 pages are devoted to this aspect with 17 separate contributions from 24 authors. The range covered extends from graphite to non-metal and to metal whiskers, even to the study of ferromagnetic domains in iron whiskers. Effects of irradiation, etching, straining, electrochemical behaviour, plastic deformation and indeed a whole host of aspects are reported on. Some admirable electron-microscope pictures are reproduced. An outstanding contribution covering 84 pages is that on growth of crystal whiskers by Nabarro and Jackson, which is brilliantly illustrated and is a masterly summary with no less than 246 references. A most impressive contribution indeed.

A hundred pages (9 contributions) are concerned with crystal growth from the solvent phase. Methods are described for growing large silicon crystals largely free from dislocations. Growth of crystals of the solute phase occupies 74 pages (7 contributions) and the growth of synthetic quartz crystals is included here. Section VI which deals with crystallization of polymers ends the report with 125 pages (8 contributions). An attractive paper here is the review on Morphology of Crystalline Polymers by A. Keller, another beautifully illustrated article, also with a comprehensive bibliography. This last section also includes a valuable paper by F. P. Price on A Light Scattering Investigation of Crystal Growth in Polyethylene (a material which incidentally attracted contributions in no less than five papers).

Your reviewer marvelled at the very large numbers of

beautiful photographs of the microtopographies of crystals but was forcibly struck by the *complete absence* of any interferometric examinations of surface microtopographies. This seems a remarkable failing in a research field of this character. Why use *two-dimensional* microscopy only, when *three-dimensional* microscopy is available? Is it that experimenters have not yet realized that multiple-beam interferometry offers three-dimensional microscopy? Or is a more plausible explanation that as yet crystal morphology specialists, as such, have not yet learnt the necessary optical techniques of multiple-beam interferometry?

Any one engaged on any branch of crystal growth is well advised to dip into this volume. Somewhere in the mass of information presented he will find something of personal interest. There is very little on X-ray structure; the reports are more concerned with morphology.

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Gleichgewichts- und Wachstumsformen von Kristallen. By Dr B. HONIGMANN. Pp. 154. Darmstadt: Dr Dietrich Steinkopff Verlag, 1958. Price DM. 26-00.

This short work is presented strictly from the point of view of I. N. Stranski and his students, of whom the author is one. Such a work is valuable in that it enables one to study the point of view of this school by reading a single source, but it also suffers from the limitations of this point of view.

The strong points of this book are the tables and figures presenting experimental data concerning the habit of many simple crystals, and the brief section on experimental determinations of crystal growth rates. Even in these sections the data have been carefully selected. Much important work by English and American authors on growth forms and rates has been omitted. In fact, the great impact dislocation theory has had on the crystal growth theory and the interpretation of experimental results has been drastically minimized. Furthermore, in the opinion of this reviewer, no modern discussion of growth forms of crystals, no matter how brief, should exclude all references to 'whisker' growth.

The last section of the book is devoted to the theory of crystal growth and the development of equilibrium forms as presented by I. N. Stranski and his students over the past thirty years. This theory is correct insofar as the assumptions on which it is based are correct. However, if there is a large body of experimental data demonstrating that it applies to the growth of real crystals, the author does not present it. This is especially the case in the discussion of the effect of impurities on growth habit. In this case, the many publications concerned with this problem were, for the most part, ignored, and no comparison of theory with the few data presented is attempted.

There is a fairly complete bibliography at the end of the work which includes many references only mentioned in the text.

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